

R1WV3216R Series

32Mb Advanced LPSRAM (2M wordx16bit)

REJ03C0215-0300Z Rev.3.00 2008.03.03

Description

The R1WV3216R Series is a family of low voltage 32-Mbit static RAMs organized as 2097152-words by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1WV3216R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1WV3216R Series is made by stacked-micro-package technology and two chips of 16Mbit Advanced LPSRAMs are assembled in one package.

The R1WV3216R Series is packaged in a 52pin micro thin small outline mount device[μ TSOP / 10.79mm x 10.49mm with the pin-pitch of 0.4mm] or a 48balls fine pitch ball grid array [f-BGA / 7.5mmx8.5mm with the ball-pitch of 0.75mm and 6x8 array] . It gives the best solution for a compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7-3.6V power supply
- Small stand-by current:4µA (3.0V, typ.)
- Data retention supply voltage =2.0V
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie capability
- OE# prevents data contention on the I/O bus
- Process technology: 0.15um CMOS



Ordering Information

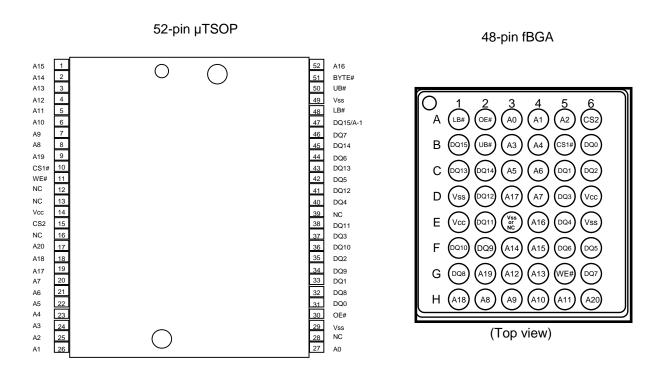
Type No.	Access time	Package
R1WV3216RSD-7S%	70 ns	350-mil 52-pin plastic μ - TSOP(II)
R1WV3216RSD-8S%	85 ns	(normal-bend type) (52PTG)
R1WV3216RBG-7S%	70 ns	7.5mmv9.5mm f.DCA 0.75mm nitch 49hall
R1WV3216RBG-8S%	85 ns	7.5mmx8.5mm f-BGA 0.75mm pitch 48ball

% - Temperature version; see table below

%	Temperature Range
R	0 ~ +70 °C
I	-40 ~ +85 °C



Pin Arrangement

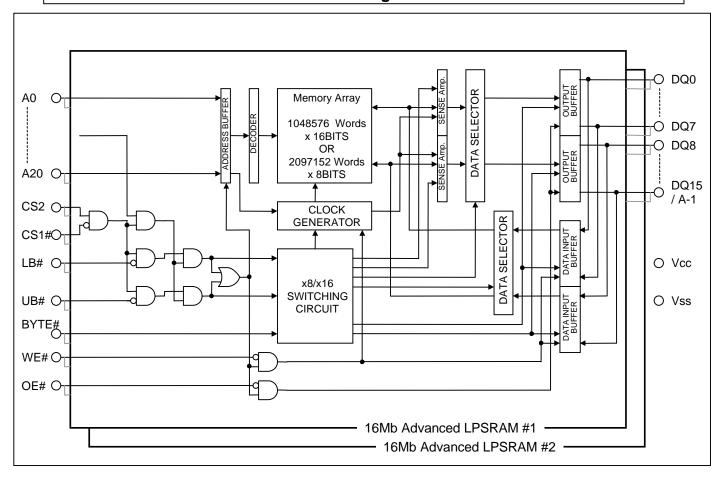


Pin Description						
Pin name	Function					
A0 to A20	Address input (Word mode)					
A-1 to A20	Address input (Byte mode)					
DQ 0 to DQ15	Data input/output					
CS1# &CS2	Chip select					
WE#	Write enable					
OE#	Output enable					
LB#	Lower byte select					
UB#	Upper byte select					
Vcc	Power supply					
Vss	Ground					
BYTE#	Byte (x8 mode) enable input					
NC	Non connection					

Note: Byte Mode is supported by only 52-pin μ TSOP type.



Block Diagram



Note: BYTE# pin is supported by only 52-pin μ TSOP type.



Operating Table

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0-7	DQ8-14	DQ15	Operation
Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by
Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by
Х	Х	Н	Η	Н	Х	Χ	High-Z	High-Z	High-Z	Stand by
L	Н	Н	L	Н	L	Х	Din	High-Z	High-Z	Write in lower byte
L	Н	Н	L	Н	Н	L	Dout	High-Z	High-Z	Read from lower byte
L	Н	Х	Х	Х	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	Н	L	L	Χ	High-Z	Din	Din	Write in upper byte
L	Н	Н	Н	L	Н	L	High-Z	Dout	Dout	Read from upper byte
L	Н	Н	L	L	L	Χ	Din	Din	Din	Write
L	Н	Н	L	L	Н	L	Dout	Dout	Dout	Read
L	Н	L	L	L	L	Х	Din	High-Z	A-1	Write
L	Н	L	L	Ĺ	Н	L	Dout	High-Z	A-1	Read

Note 1. H:VIH L:VIL X: VIH or VIL

Absolute Maximum Ratings

Parameter	Symbol		Value	Unit
Power supply voltage relative to Vss	Vcc		-0.5 to +4.6	
Terminal voltage on any pin relation toVss	VT	-0.5	*1 to Vcc+0.3*2	V
Power dissipation	Рт		0.7	W
On a ration to represent us	Tons	R ver. *3	0 to +70	°C
Operation temperature	Topr	I ver. *3	-40 to +85	°C
Storage temperature	Tstg		-65 to +150	°C
Storage temperature range under bice	Thios	R ver. *3	0 to +70	°C
Storage temperature range under bias	Tbias	l ver. *3	-40 to +85	°C

Note 1: -2.0V in case of AC (Pulse width \leq 30ns)

2: Maximum voltage is +4.6V

3: Temperature range depends on R/I-version. Please see table on page 2.



^{2.} BYTE# pin is supported by only 52-pin μTSOP type. When apply BYTE# ="L", please assign LB#=UB#="L".

Recommended Operating Conditions

Parameter	Parameter		Min.	Тур.	Max.	Unit	Note
Supply voltage	O and allows		2.7	3.0	3.6	V	
Supply voltage		Vss	0	0	0	V	
Input high voltage		VIH	2.4	-	Vcc+0.2	V	
Input low voltage		VIL	-0.2	-	0.4	V	1
Ambient temperature range	R ver.	To	0	-	+70	°C	2
Ambient temperature range	I ver.	Та	-40	-	+85	°C	2

Note 1. –2.0V in case of AC (Pulse width \leq 30ns)

DC Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions*3
Input leakage current	lu			1	μΑ	Vin=Vss to Vcc
Output leakage current	l _{Lo}	ı	ı	1	μΑ	BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V, CS1# =VIH or CS2=VIL or OE# = VIH or WE# =VIL or LB# =UB# =VIH,VI/O=Vss to Vcc
A. coro no on orotin o	Icc ₁		30 *1	55	mA	BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V, Min. cycle, duty =100% I I/O = 0 mA, CS1# =VIL, CS2=VIH Others = VIH / VIL
Average operating current	lcc2	-	3 *1	8	mA	BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V, Cycle time = 1 μ s, I I/O = 0 mA, CS1# \leq 0.2V, CS2 \geq VCC-0.2V VIH \geq VCC-0.2V , VIL \leq 0.2V, duty=100%
Standby current	Isb	ı	0.1 *1	0.3	mA	BYTE# ≥Vcc-0.2V or BYTE#≤0.2V, CS2=VIL
		ı	4 *1	12	μΑ	~+25°C V in ≥ 0V, BYTE# ≥Vcc-0.2V or
		ı	7 *2	24	μΑ	~+40°C BYTE#≤0.2V, (1) 0V≤CS2≤0.2V or (2) CS2≥Vcc-0.2V,
Standby current	Isb1	1	ı	50	μA	~+70°C (2) CS2≥VC-0.2V, CS1# ≥Vcc-0.2V or (3)LB# =UB# ≥Vcc-0.2V, CS2≥Vcc-0.2V,
		-	-	80	μΑ	~+85°C CS1# ≤0.2V Average value
Output high voltage	Vон	2.4	-	-	V	BYTE# ≥Vcc-0.2V or BYTE#≤0.2V, IOH = -1mA
Output Low voltage	Vol	1	-	0.4	V	BYTE# ≥Vcc-0.2V or BYTE#≤0.2V, IOL = 2mA

Note 1. Typical parameter indicates the value for the center of distribution at Vcc=3.0V (Ta= 25°C), and not 100% tested.

^{3.} BYTE# pin is supported by only 52-pin μ TSOP type.



^{2.} Ambient temperature range depends on R/I-version. Please see table on page 2.

^{2.} Typical parameter indicates the value for the center of distribution at Vcc=3.0V (Ta= 40°C), and not 100% tested.

Capacitance

 $(Ta = +25^{\circ}C, f = 1MHz)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	20	рF	V in = 0V	1
Input / output capacitance	C 1/O	-	-	20	pF	V I/O = 0V	1

Note 1. This parameter is sampled and not 100% tested.

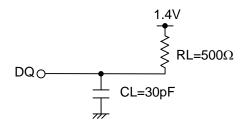
AC Characteristics

Test Conditions (Vcc= $2.7 \sim 3.6 \text{V}$, Ta = $0 \sim +70 ^{\circ}\text{C} / -40 \sim +85 ^{\circ}\text{C}$ *)

• Input pulse levels: VIL= 0.4V,VIH=2.4V

• Input rise and fall time: 5ns

Input and output timing reference levels: 1.4V
Output load: See figures (Including scope and jig)



Note: Temperature range depends on R/I-version. Please see table on page 2.



Read Cycle

Doromotor	Cumbal	R1WV32	16R**-7S	R1WV32	16R**-8S	Unit	Notes
Parameter	Symbol	Min.	Max.	Min.	Max.	Unit	notes
Read cycle time	t RC	70	-	85	-	ns	
Address access time	t AA	1	70	1	85	ns	
Chin palest access time	t ACS1	1	70	1	85	ns	
Chip select access time	t ACS2	-	70	-	85	ns	
Output enable to output valid	t oe	ı	35	-	45	ns	
Output hold from address change	t он	10	-	10	-	ns	
LB#,UB# access time	t BA	-	70	-	85	ns	
Chip select to output in low-Z	t clz	10	-	10	-	ns	2,3
LB#,UB# enable to low-Z	t BLZ	5	-	5	-	ns	2,3
Output enable to output in low-Z	t olz	5	-	5	-	ns	2,3
Ohio decelerate sutrestic high 7	t CHZ1	0	25	0	30	ns	1,2,3
Chip deselect to output in high-Z	t CHZ2	0	25	0	30	ns	1,2,3
LB#,UB# disable to high-Z	t BHZ	0	25	0	30	ns	1,2,3
Output disable to output in high-Z	t onz	0	25	0	30	ns	1,2,3



Write Cycle

Parameter	Symbol	R1WV32	16R**-7S	R1WV32	16R**-8S	Unit	Notes
Parameter	Symbol	Min.	Max.	Min.	Max.	Unit	notes
Write cycle time	t wc	70	-	85	-	ns	
Address valid to end of write	t aw	65	-	70	-	ns	
Chip selection to end of write	t cw	65	-	70	-	ns	5
Write pulse width	twp	55	-	60	-	ns	4
LB#,UB# valid to end of write	t _{BW}	65	-	70	-	ns	
Address setup time	t AS	0	-	0	-	ns	6
Write recovery time	twr	0	-	0	-	ns	7
Data to write time overlap	tow	35	-	40	-	ns	
Data hold from write time	t DH	0	-	0	-	ns	
Output active from end of write	tow	5	-	5	-	ns	2
Output disable to output in high-Z	t onz	0	25	0	30	ns	1,2
Write to output in high-Z	t wHz	0	25	0	30	ns	1,2

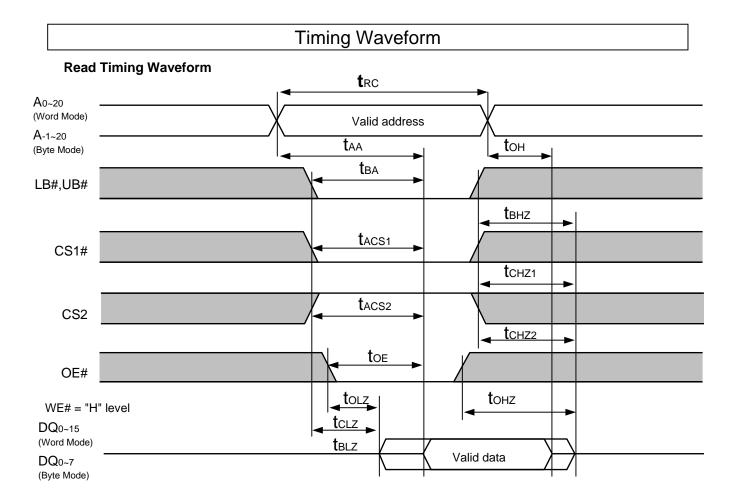
Byte Enable (supported by only 52-pin µTSOP)

Parameter	Symbol	R1WV32	16R**-7S	R1WV32	16R**-8S	Unit	Notes
Farameter	Symbol Min. Max.		Min.	Max.	Offic	Notes	
Byte setup time	t BS	5	-	5	-	ms	
Byte recovery time	t BR	5	-	5	-	ms	

Note 1. tchz, tohz, twhz and tbhz are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

- 2. This parameter is sampled and not 100% tested.
- 3. AT any given temperature and voltage condition, thz max is less than tLz min both for a given device and form device to device.
- 4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low.
 - A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. twp is measured from the beginning of write to the end of write.
- 5. tcw is measured from the later of CS1# going low or CS2 going high to end of write.
- 6. tas is measured the address valid to the beginning of write.
- 7. twn is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

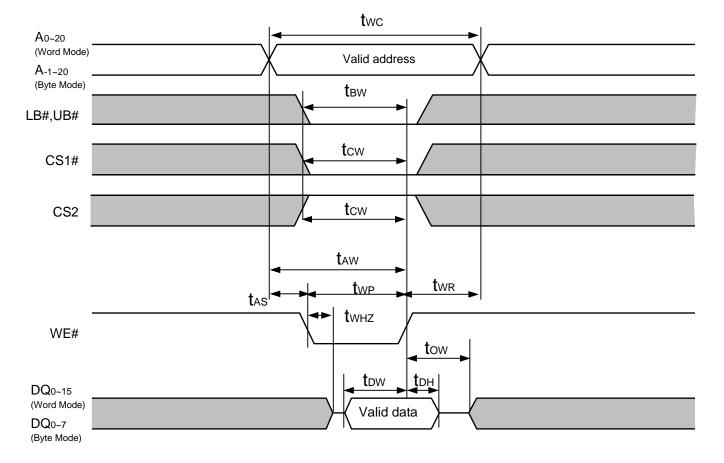




Note: Byte Mode is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V



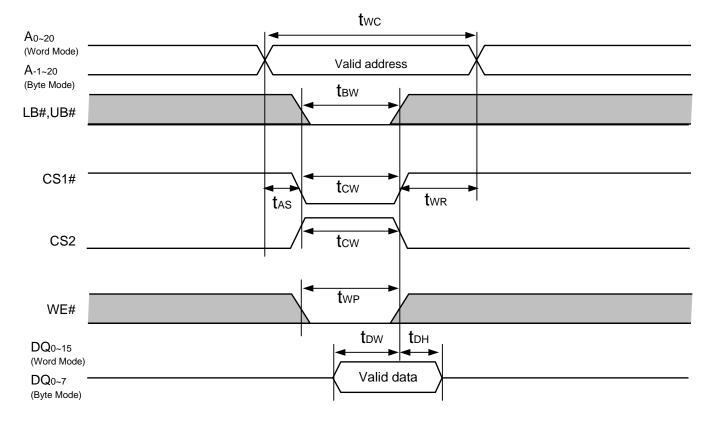
Write Timing Waveform (1) (WE# CLOCK)



Note: Byte Mode is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V



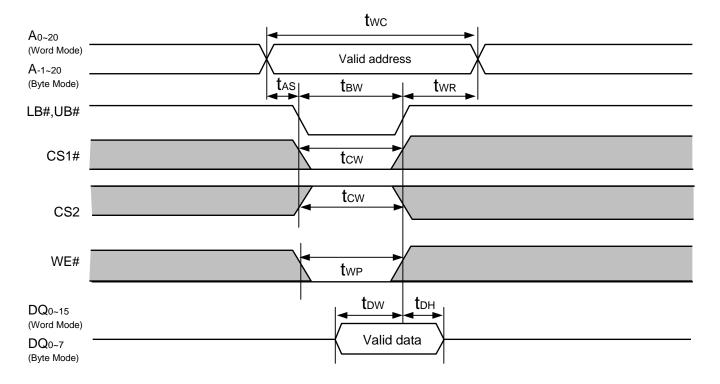
Write Timing Waveform (2) (CS1#, CS2 CLOCK, OE#=VIH)



Note: Byte Mode is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

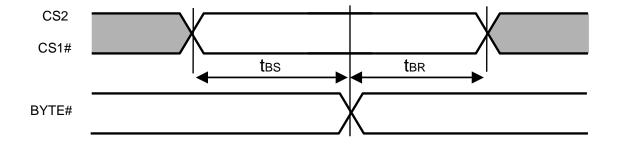


Write Timing Waveform (3) (LB#,UB# CLOCK, OE#=VIH)



Note: Byte Mode is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

BYTE# Timing Waveform





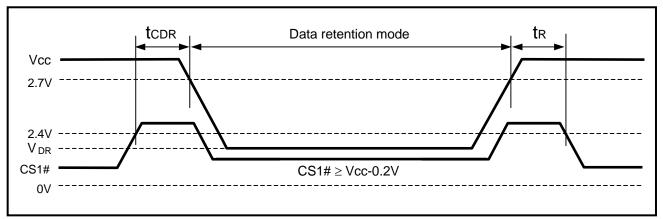
Data Retention Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions*3,4		
Vcc for data retention	Vdr	2.0	1	3.6	٧	$\label{eq:continuous_problem} \begin{split} &V \text{ in } \ge \text{OV}, \\ &\text{BYTE} \# \ge \text{Vcc-0.2V or BYTE} \# \le \text{0.2V} \\ &(1) \text{ OV} \le \text{CS2} \le \text{0.2V or} \\ &(2) \text{ CS2} \ge \text{Vcc-0.2V}, \\ &\text{CS1} \# \ge \text{Vcc-0.2V or} \\ &(3) \text{ LB} \# = \text{UB} \# \ge \text{Vcc-0.2V}, \\ &\text{CS2} \ge \text{Vcc-0.2V}, \\ &\text{CS1} \# \le \text{0.2V} \end{split}$		
		ı	4 *1	12	μA	~+25°C	Vcc=3.0V,Vin≥0V, BYTE# ≥ Vcc-0.2V or	
		ı	7 *2	24	μA	~+40°C	BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS2 ≥ Vcc-0.2V,	
Data retention current	ICC DR	1	1	50	μΑ	~+70°C	004# > 1/22 0 01/ 22	
		ı	ı	80	μA	~+85°C	CS2 ≥ Vcc-0.2V, CS1# ≤ 0.2V Average value	
Chip deselect to data retention time	t CDR	0	•	-	ns	On a set set in a set see		
Operation recovery time	t R	5	-	-	ms	See r	etention waveform	

- Note 1. Typical parameter indicates the value for the center of distribution at Vcc=3.0V ($Ta=25^{\circ}C$) and not 100% tested.
 - 2. Typical parameter indicates the value for the center of distribution at Vcc=3.0V (Ta= 40°C) and not 100% tested.
 - 3. BYTE# pin is supported by only 52-pin µTSOP type.
 - 4. Also CS2 controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer .If CS2 controls data retention mode,Vin levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ Vcc-0.2V or 0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state.

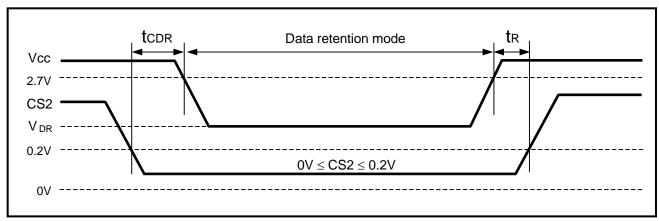


Low Vcc Data Retention Timing Waveform (1) (CS1# Controlled)



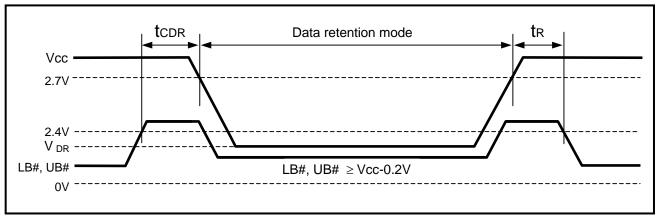
Note: BYTE# pin is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

Low Vcc Data Retention Timing Waveform (2) (CS2 Controlled)



Note: BYTE# pin is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

Low Vcc Data Retention Timing Waveform (3) (LB#, UB# Controlled)



Note: BYTE# pin is supported by only 52-pin μ TSOP type. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V



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450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

Old Company Name in Catalogs and Other Documents

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April 1st, 2010 Renesas Electronics Corporation

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